
2SH30

Silicon N Channel IGBT
High Speed Power Switching

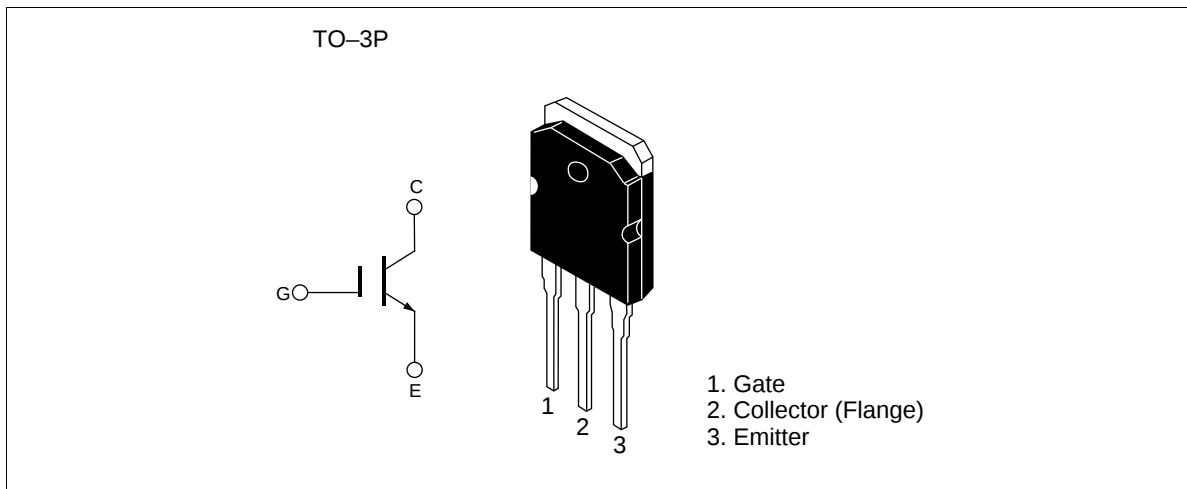
HITACHI

ADE-208-792A(Z)
2nd. Edition
May 1999

Features

- High speed switching
- Low on-voltage

Outline



2SH30

Absolute Maximum Ratings (Ta = 25°C)

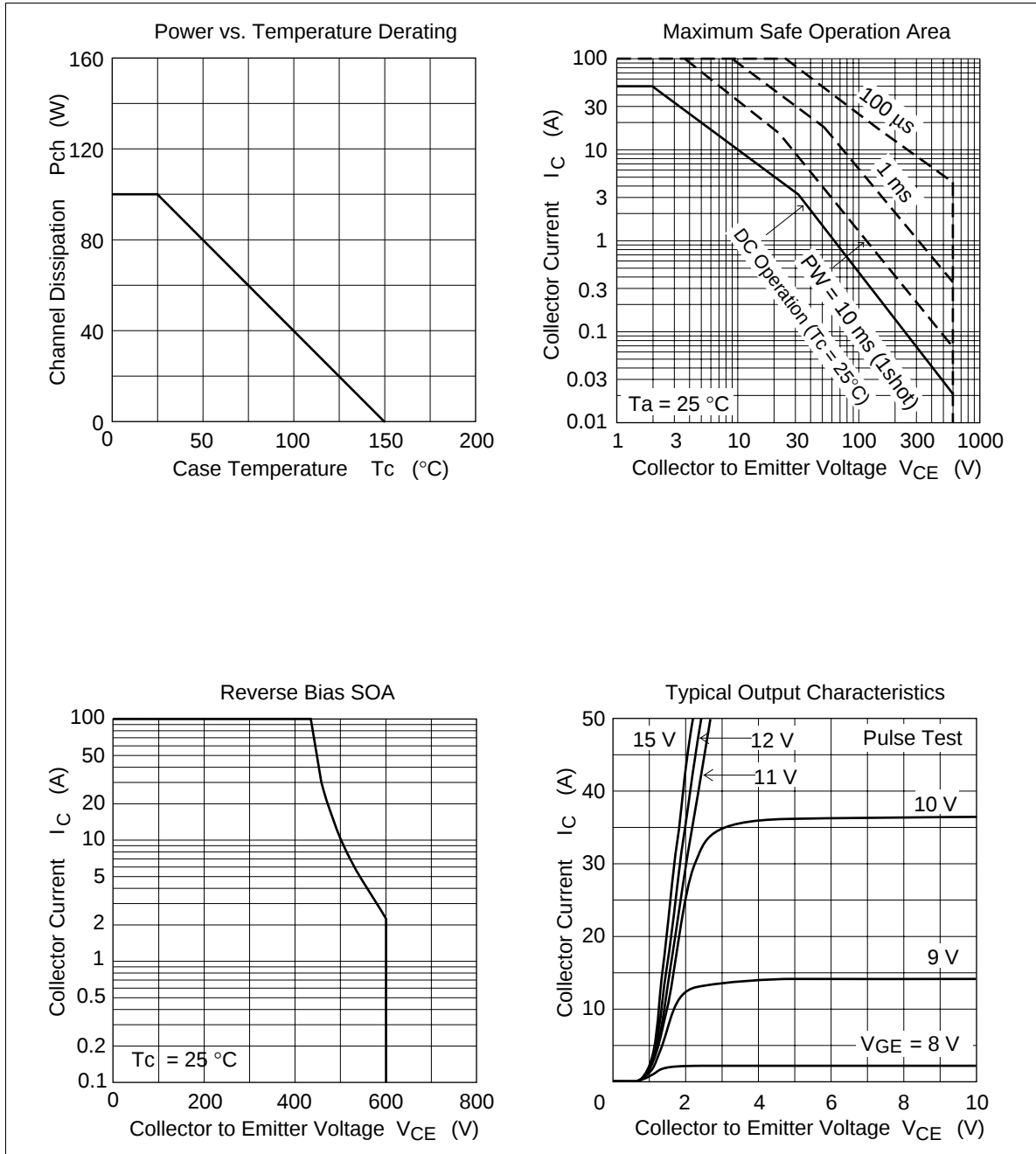
Item	Symbol	Ratings	Unit
Collector to Emitter voltage	V_{CES}	600	V
Gate to Emitter voltage	V_{GES}	± 20	V
Collector current	I_C	50	A
Collector peak current	$i_{c(peak)}$	100	A
Collector dissipation	P_C ^{Note1}	100	W
Channel temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

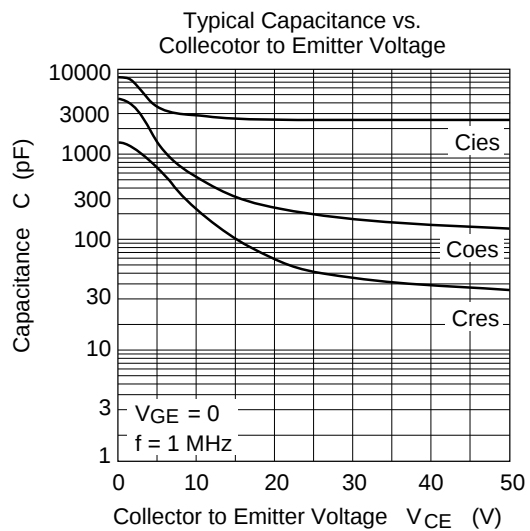
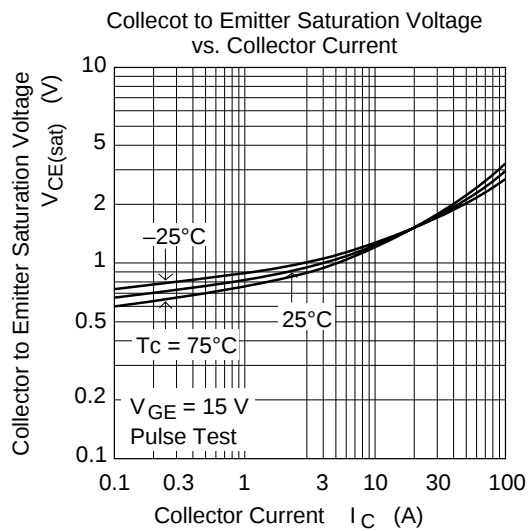
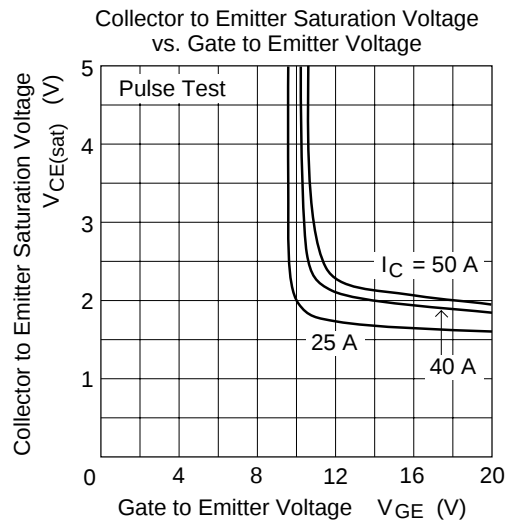
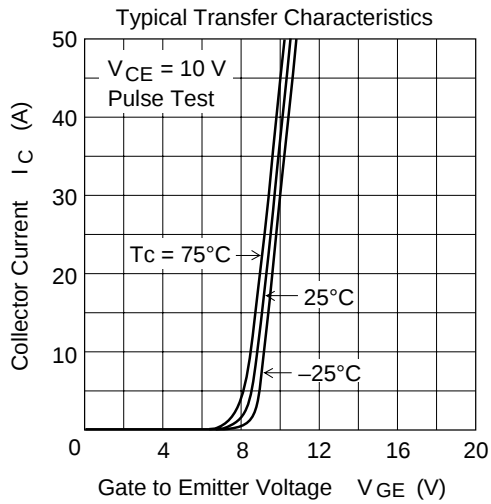
Note: 1. Value at $T_C = 25^\circ\text{C}$

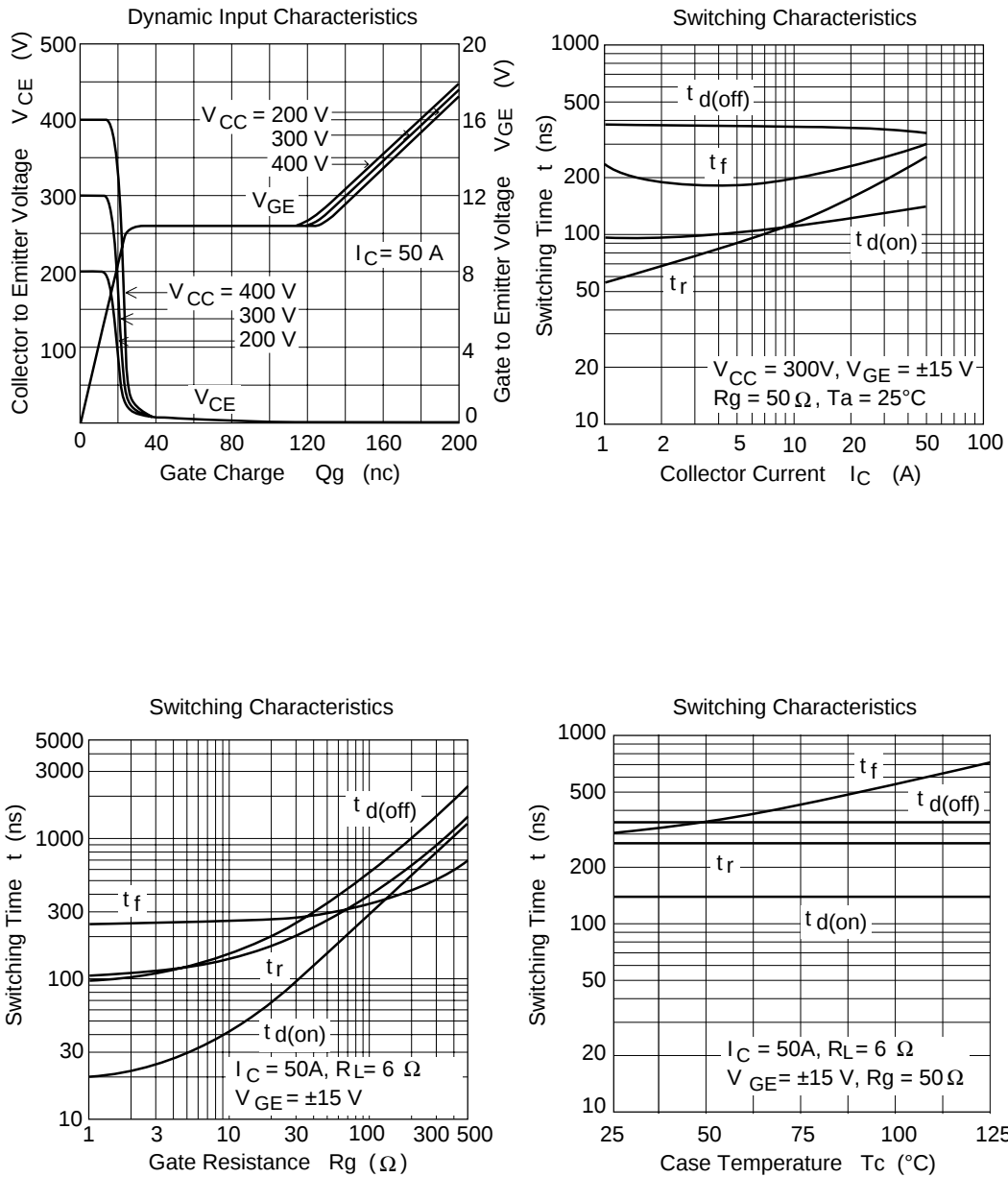
Electrical Characteristics (Ta = 25°C)

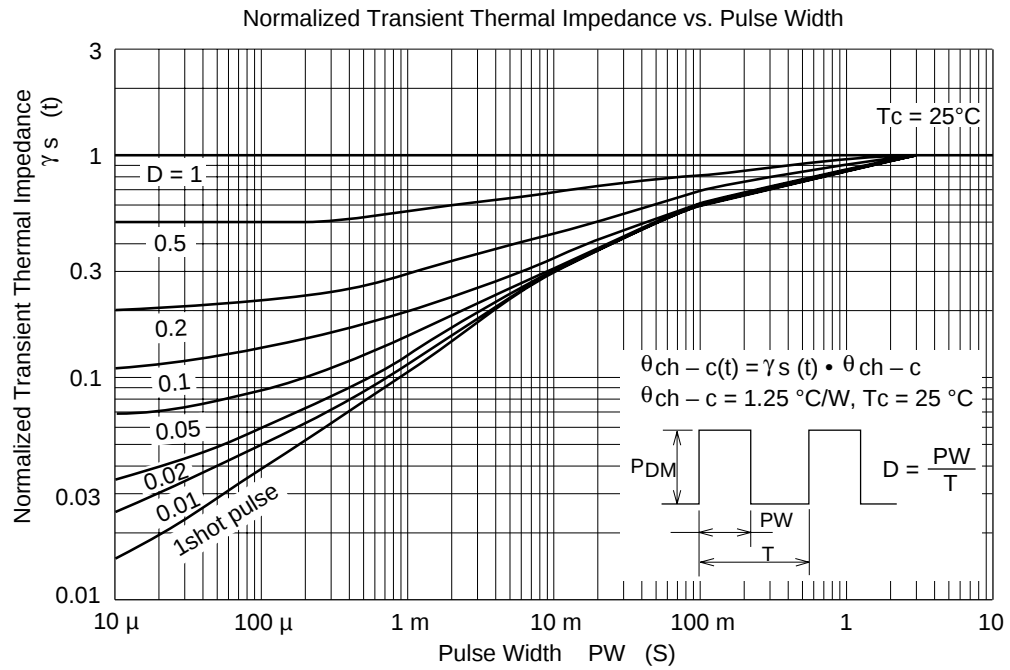
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero gate voltage collector current	I_{CES}	—	—	250	μA	$V_{CE} = 600\text{V}$, $V_{GE} = 0$
Gate to emitter leak current	I_{GES}	—	—	± 1	μA	$V_{GE} = \pm 20\text{V}$, $V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(off)}$	6.0	—	8.0	V	$I_C = 50\text{mA}$, $V_{CE} = 10\text{V}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	2.1	2.6	V	$I_C = 50\text{A}$, $V_{GE} = 15\text{V}$
Input capacitance	C_{ies}	—	2800	—	pF	$V_{CE} = 10\text{V}$, $V_{GE} = 0$ $f = 1\text{MHz}$
Switching time	t_r	—	280	—	ns	$I_C = 50\text{A}$
	t_{on}	—	430	—	ns	$R_L = 6\ \Omega$
	t_f	—	300	600	ns	$V_{GS} = \pm 15\text{V}$
	t_{off}	—	650	1300	ns	$R_g = 50\ \Omega$

Main Characteristics

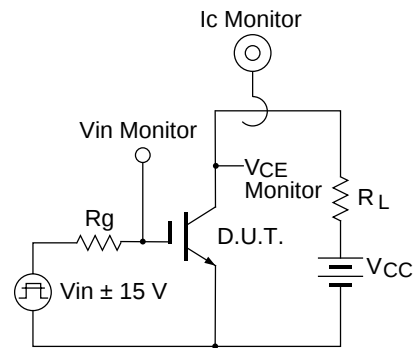




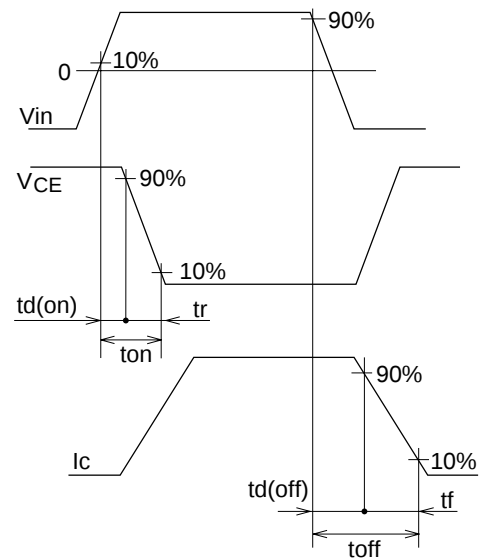




Switching Time Test Circuit

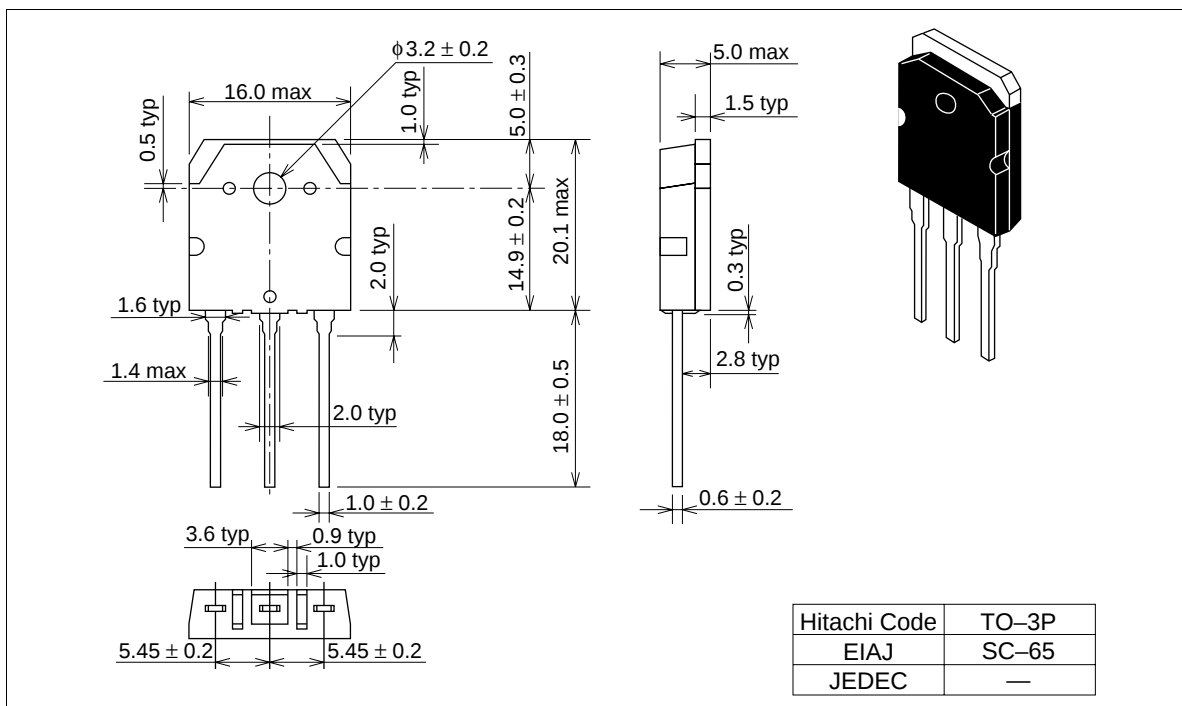


Waveform



Package Dimensions

Unit: mm



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